



Silicon Rectifier Cells

with polysiloxan passivation

AG 3A ... AG3M

Forward Current: 3 A

Reverse Voltage: 50 to 1000 V

Publish Data

Features

Mechanical Data

- Weight approx. 0.3g
- ²⁾ $I_F = 3A$, $T_j = 25^\circ C$

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time $I_F = A$ $I_R = A$ $I_{RR} = A$ t_{rr} ns	Max. forward voltage $V_F^{2)}$
AG 3A	50	80	/	<1,2
AG 3B	100	130	/	<1,2
AG 3D	200	250	/	<1,2
AG 3G	400	450	/	<1,2
AG 3J	600	700	/	<1,2
AG 3K	800	1000	/	<1,2
AG 3M	1000	1300	/	<1,2

Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise specified

Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 100^\circ C$ ¹⁾	3	A
I_{FRM}	Repetitive peak forward current $f > 15 Hz$ ¹⁾	30	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	150	A
i^2t	Rating for fusing, $t < 10 ms$ ³⁾	110	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾		K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾		K/W
T_j	Operating junction temperature	-50 ... +150°C	°C
T_s	Storage temperature	-50 ... +150°C	°C

Characteristics $T_c = 25^\circ C$ unless otherwise specified

Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25^\circ C$; $V_R = V_{RRM}$	10	μA
	$T_j = 100^\circ C$; $V_R = V_{RRM}$	1	mA
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $di_F/dt = A/ms$)		μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_j = ^\circ C$; inductive load switched off)		mJ



